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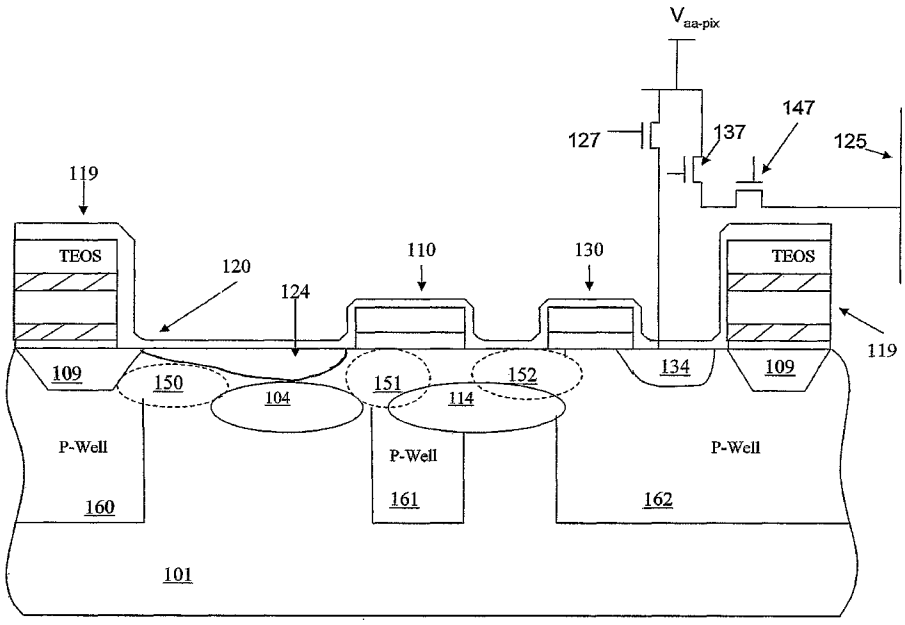
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(54) Title: METHOD OF FABRICATING A STORAGE GATE PIXEL DESIGN



(57) Abstract: A method of fabricating a pixel cell having a shutter gate structure. First and second charge barriers are respectively created between a photodiode and a first charge storage region and between the first storage region and a floating diffusion region. A global shutter gate is formed to control the charge barrier and transfer charges from the photodiode to the first charge storage region by effectively lowering the first charge barrier. A transfer transistor acts to transfer charges from the first storage region to the floating diffusion region by reducing the second charge barrier.

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